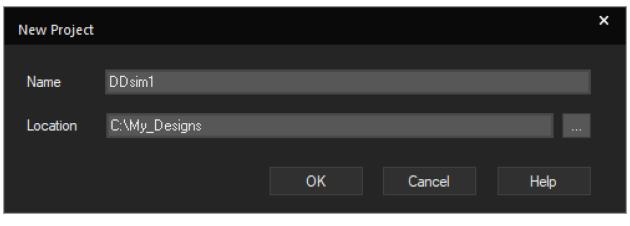
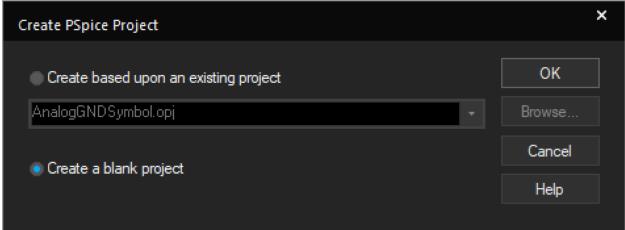
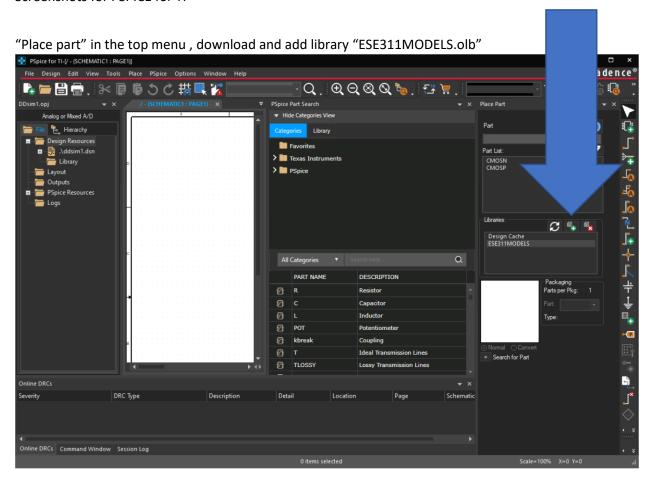
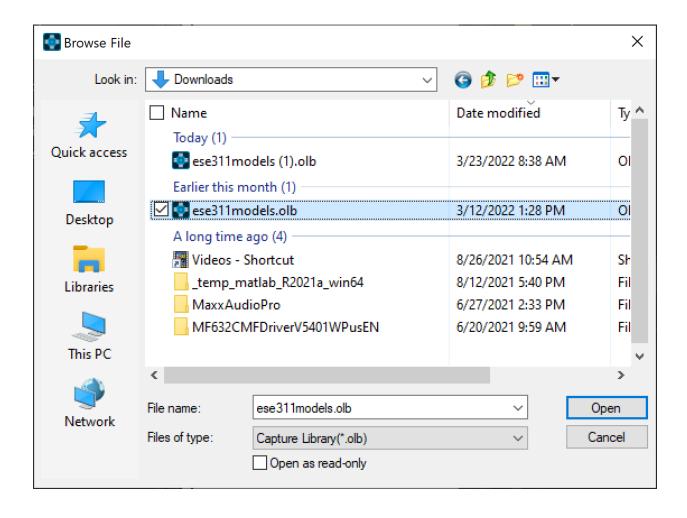
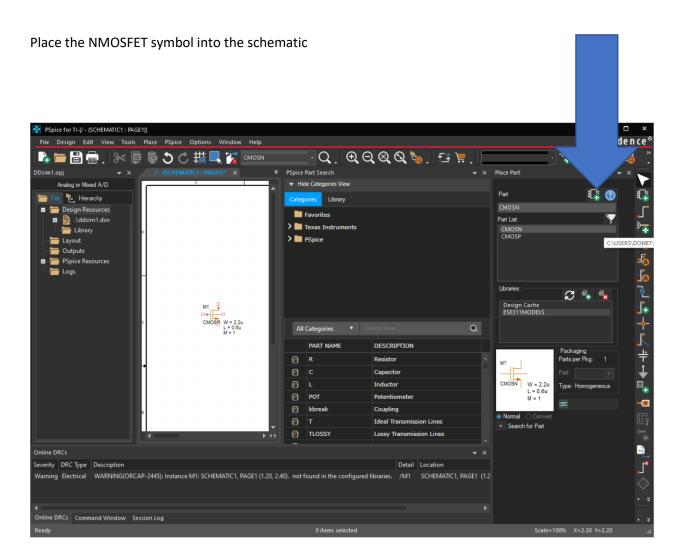
## Screenshots for PSPICE for TI



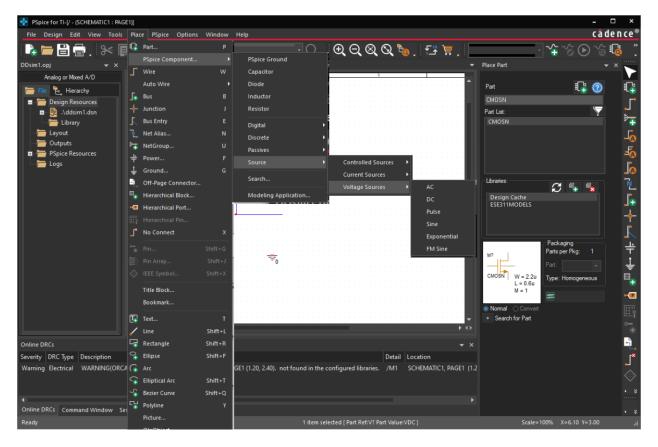






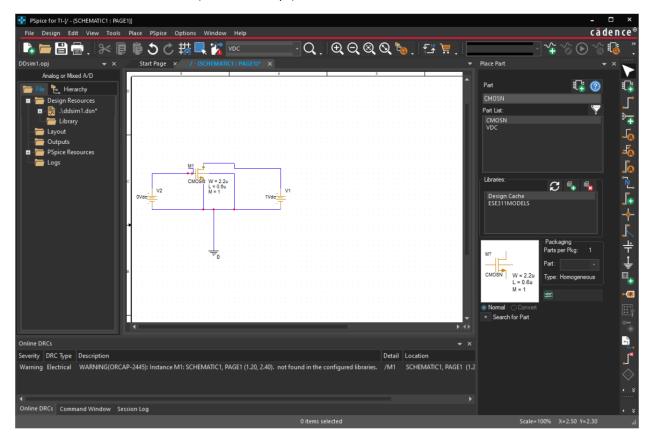


Obtain the schematic for Simulation 1: place PSPICE components: ground with 0, two DC voltage sources.

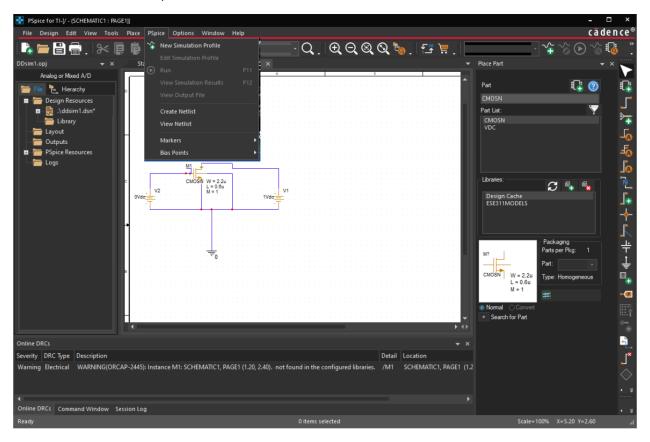


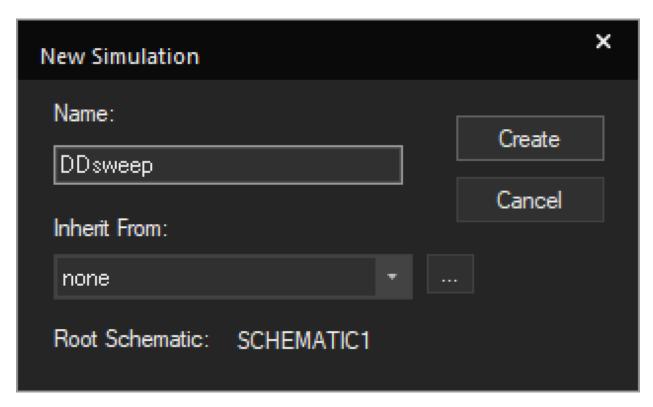
Click and adjust DC voltage: set 1V for the drain to source voltage V1.

V2 can be left at 0 at this time (it will be swept)

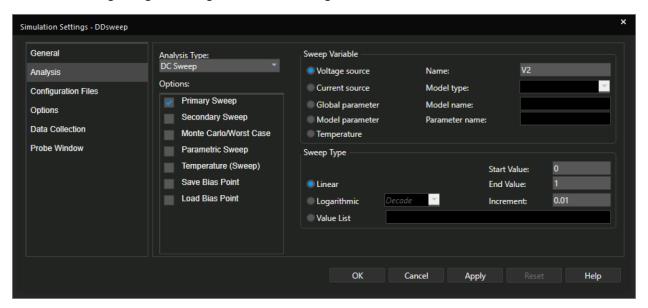


## Create a new simulation profile

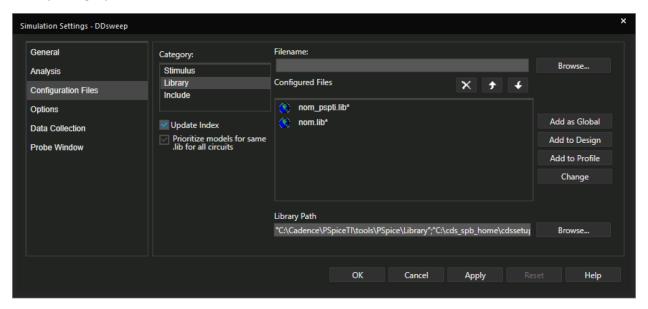


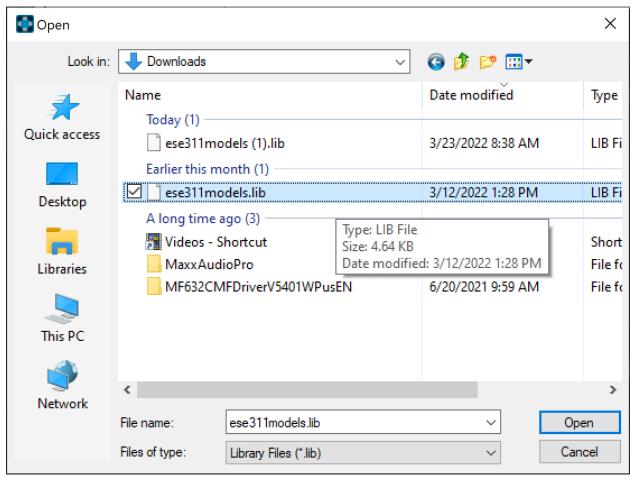


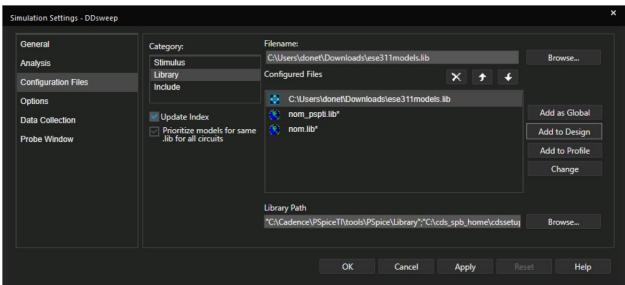
Set the DC voltage range for the gate to source voltage source V2



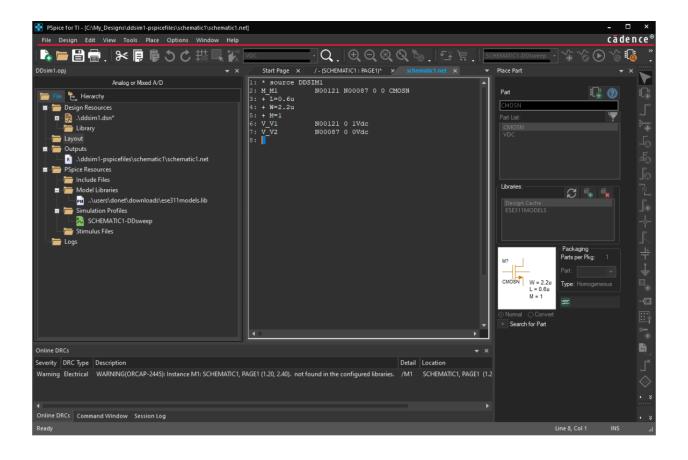
Download the MOSFET models (ESE311models.lib), show a path to the file and "Add to Design" in the Library Category



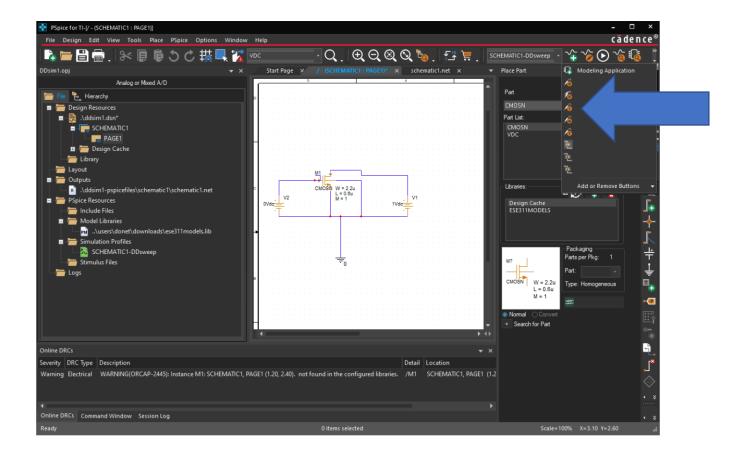




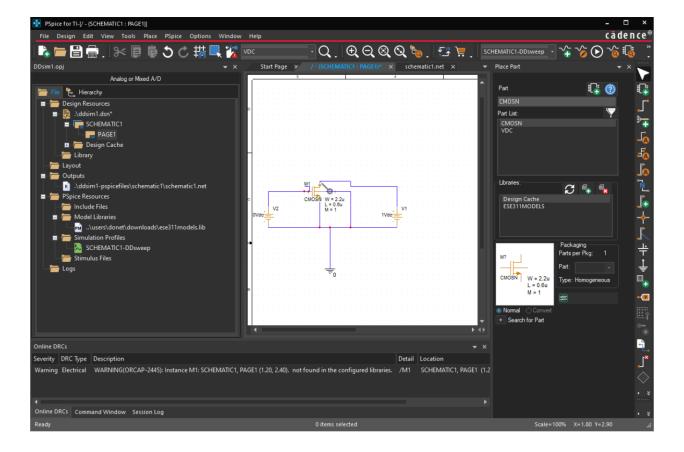
The Hierarchy window should show the lib file in PSPICE resources under Model Libraries folder



Place a DC current probe into the MOSFET drain terminal

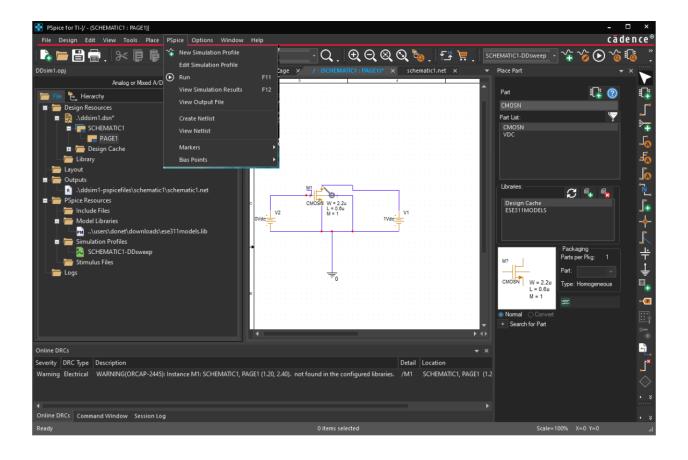


The complete schematic with the DC current probe at the drain terminal: ready to simulate



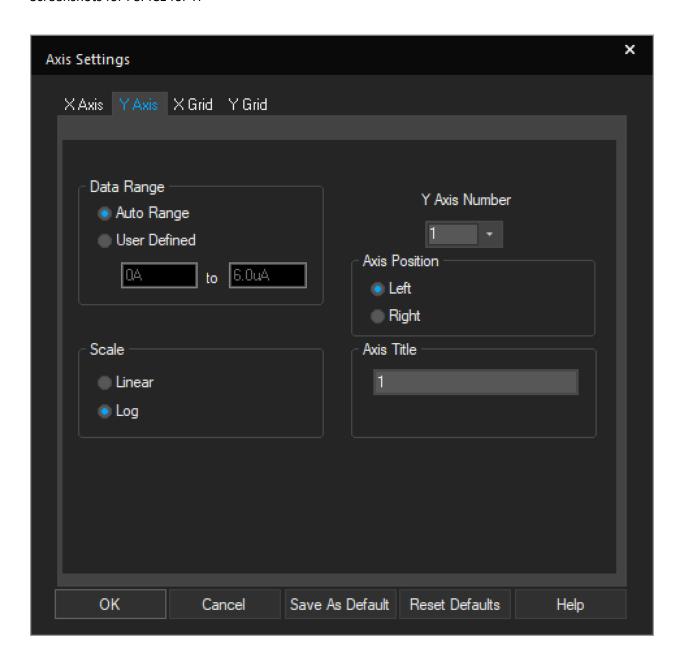
## Screenshots for PSPICE for TI

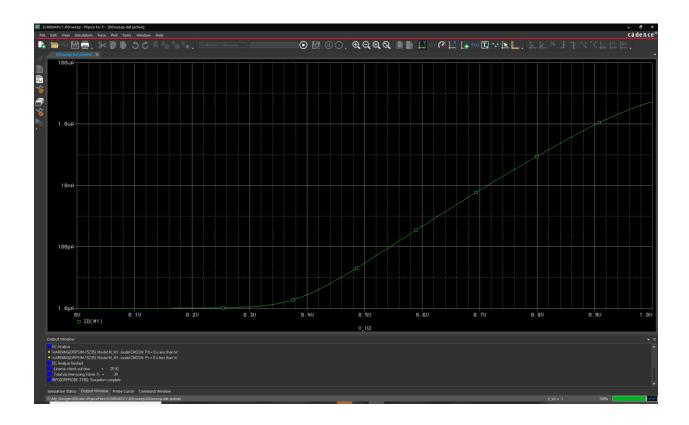
## Run the simulation (F11)





Click Y axis and change the scale to log





Output characteristics can be obtained similarly. A family of output characteristics are obtained by sweeping two DC sources: specify voltage ranges and increments for the primary and secondary sweeps.